



DMT47M2SFVWQ

40V 150°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
40V	7.5mΩ @ V _{GS} = 10V	49.1A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

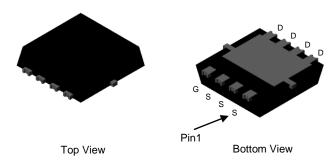
- Motor Control
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Excellent Q_{GD} × R_{DS(ON)} Product (FOM)
- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- 100% Unclamped Inductive Switching, Test in Production Ensures More Reliable and Robust End Application
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208(3)
- Weight: 0.072 grams (Approximate)



PowerDI3333-8 (SWP) (Type UX)

G Equivalent Circuit

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Ordering Information (Note 5)

	Part Number	Case	Packaging		
	DMT47M2SFVWQ-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape & Reel		
	DMT47M2SFVWQ-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape & Reel		
Notes:	: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.				

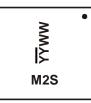
No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





Maximum Ratings (@T_A =+ 25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	40	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 7), $V_{GS} = 10V$	T _C = +25°C T _C = +70°C	ID	49.1 39.2	А
Continuous Drain Current (Note 6), V _{GS} = 10V	ID	15.4 12.3	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	196	A	
Maximum Continuous Body Diode Forward Current (Note 7)	Is	30.8	A	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle =	I _{SM}	196	A	
Avalanche Current, L = 0.1mH	I _{AS}	24.7	A	
Avalanche Energy, L = 0.1mH	E _{AS}	30.5	mJ	

Thermal Characteristics

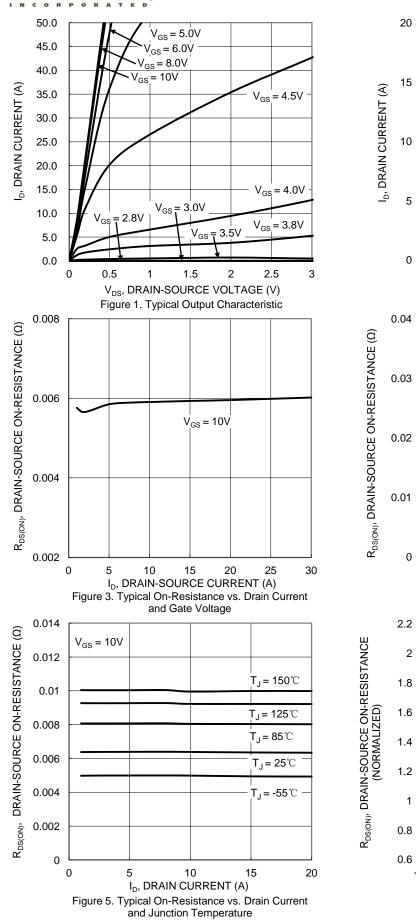
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.67	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	46.5	°C/W	
Total Power Dissipation (Note 7)	PD	27.1	W	
Thermal Resistance, Junction to Case (Note 7)	R _θ JC	4.61	°C/W	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)						÷	
Drain-Source Breakdown Voltage	BV _{DSS}	40	—	—	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	2	2.5	4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	5.9	7.5	mΩ	$V_{GS} = 10V, I_D = 20A$	
Diode Forward Voltage	V _{SD}	—	0.88	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	897		pF	$V_{DS} = 20V, V_{GS} = 0V,$ f = 1MHz	
Output Capacitance	Coss	_	530				
Reverse Transfer Capacitance	C _{rss}	—	12.4	—			
Gate Resistance	R _g	_	2.07	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Qg	_	12.1	_		$V_{DS} = 20V, I_D = 20A, V_{GS} = 10V$	
Gate-Source Charge	Q _{gs}	_	2.0	_	nC		
Gate-Drain Charge	Q _{gd}		1.9	_			
Turn-On Delay Time	t _{D(ON)}		5.36	_			
Turn-On Rise Time	t _R		4.54		1	$V_{DD} = 20V, V_{GS} = 10V,$ $R_G = 3\Omega, I_D = 20A$	
Turn-Off Delay Time	t _{D(OFF)}	_	12.1		ns		
Turn-Off Fall Time	t _F	_	5.59	_	1		
Body Diode Reverse Recovery Time	t _{RR}	_	39.1		ns		
Body Diode Reverse Recovery Charge	Q _{RR}	_	53.3	_	nC	I _F = 20A, di/dt = 100A/µs	

 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
Thermal resistance from junction to soldering point (on the exposed drain pad).
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing. Notes:





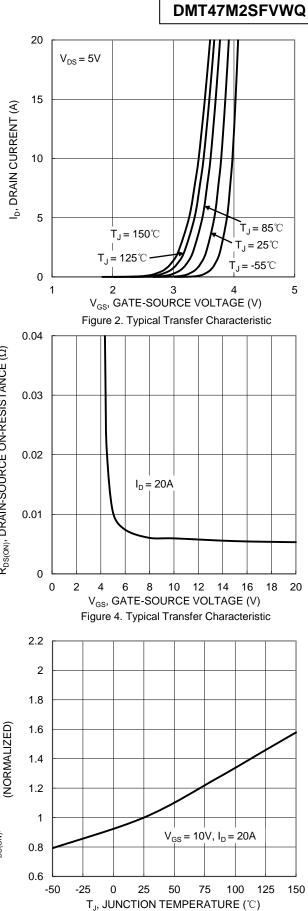
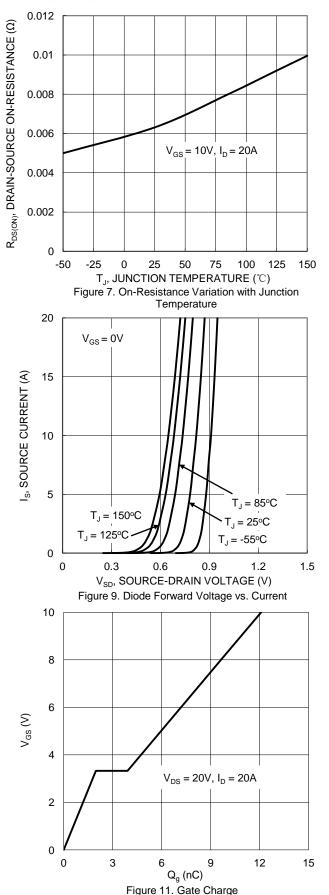


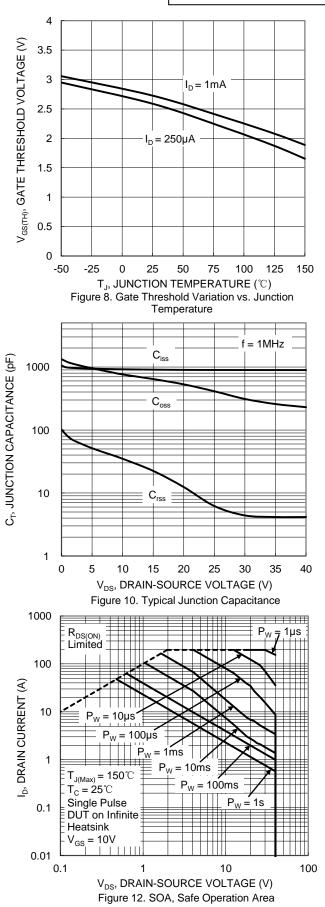
Figure 6. On-Resistance Variation with Junction

Temperature



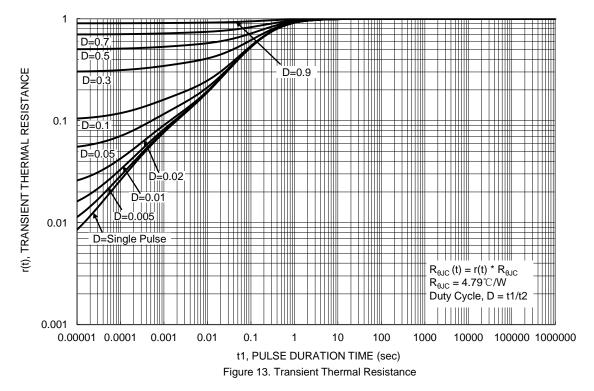






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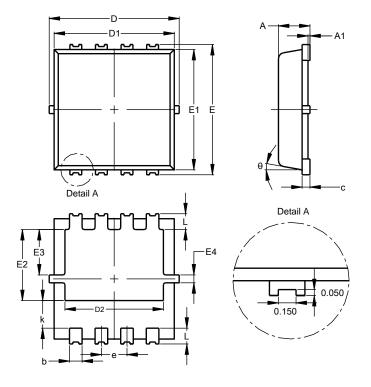




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

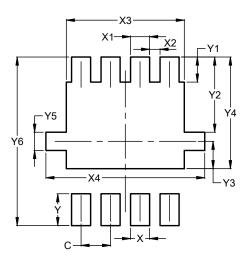


PowerDI3333-8 (SWP)						
(Type UX)						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
E	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	-	-	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All I	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700



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